

Supporting information

Modulation of N-bonding configurations and its influence on the electrical properties of nitrogen-doped graphene

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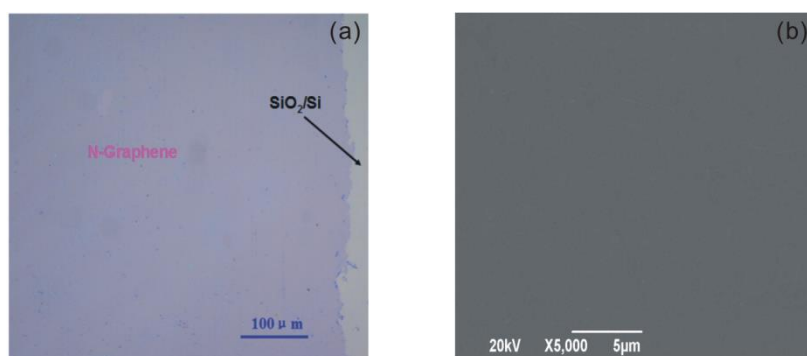


Figure S1. Optical and SEM images of nitrogen doped graphene after transferring on SiO₂/Si substrate.